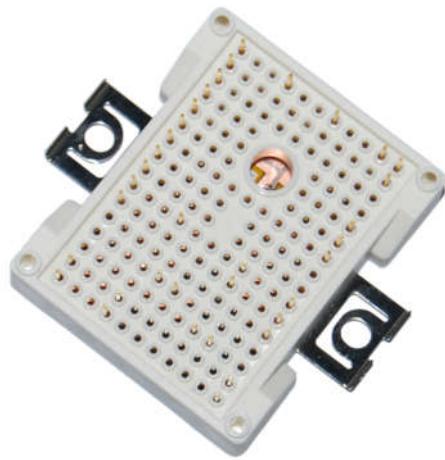


## FEATURES

- $V_{CEsat}$  with positive temperature coefficient
- Low  $V_{CEsat}$
- Low switching losses
- Low inductance case
- 10 $\mu$ s short circuit capability
- Isolated copper baseplate using DBC technology

## IGBT

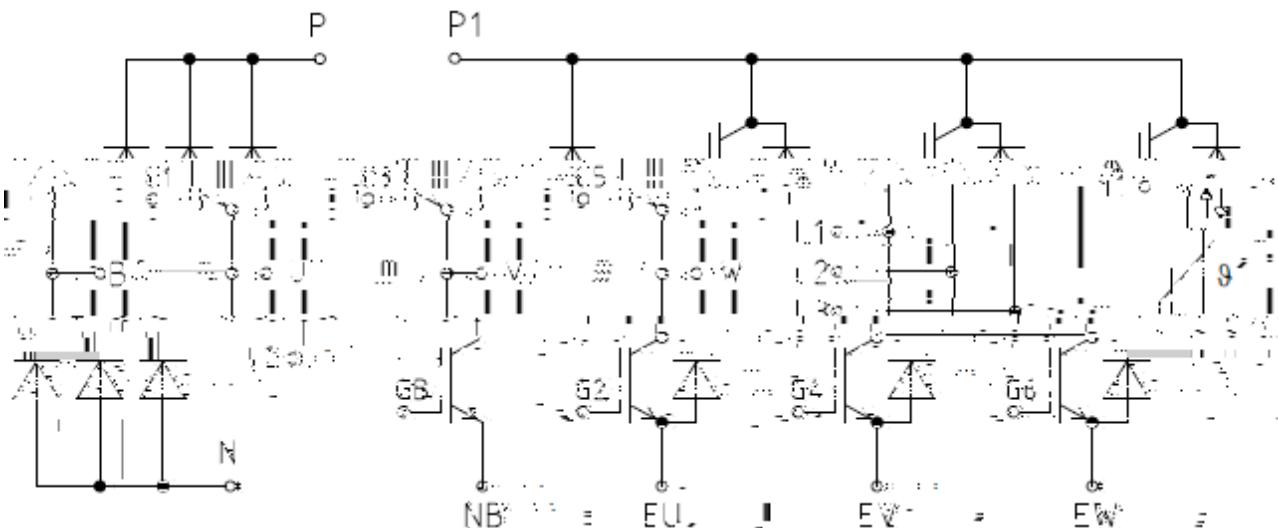
**$V_{CES} = 1200V$**   
**IC nom = 25A / ICRM = 50A**



## APPLICATION

- Inverter for motor drive Inverter
- Air Conditioning
- Auxiliary inverters
- Uninterruptible power supply

## Equivalent Circuit Schematic



**LGM25PJ120E2T1S**

**Diode, Inverter  
Maximum Rated Values**

Repetitive peak reverse voltage	Tvj = 25°C	VRRM	1200	V
Continuous DC forward current		IF	25	A
Repetitive peak forward current	t <sub>P</sub> = 1 ms	IFRM	50	A

**Characteristic Values**

Forward voltage	I <sub>F</sub> = 25 A, V <sub>GE</sub> = 0 V Tvj = 25°C Tvj = 125°C	V <sub>F</sub>	1.95 1.85		V
Peak reverse recovery current	I <sub>F</sub> = 25 A, - d <sub>iF</sub> /dt = 1200 A/μs (Tvj=150°C) V <sub>R</sub> = 600 V, V <sub>GE</sub> = -15 V Tvj = 25°C Tvj = 125°C	I <sub>RM</sub>	43 46		A
Recovered charge		Q <sub>r</sub>	1.5 2.8		μC
Reverse recovery energy		E <sub>rec</sub>	0.95 1.70		mJ
Thermal resistance, junction to case	per diode	R <sub>thJC</sub>	0.9	1.05	K/W
Thermal resistance, case to heatsink	per diode I <sub>Paste</sub> = 1 W/(m·K) / I <sub>grease</sub> = 1 W/(m·K)	R <sub>thCH</sub>	0.82		K/W
Temperature under switching conditions		T <sub>vj op</sub>	-40	150	°C

**Diode  
Maximum**

**IGBT, Brake-Chopper  
Maximum Rated Values**

Collector-emitter voltage	T <sub>vj</sub> = 25°C	V <sub>CES</sub>	1200	V
Continuous DC collector current	T <sub>c</sub> = 95°C, T <sub>vj</sub> max = 175°C	I <sub>C nom</sub>	25	A
Repetitive peak collector current	t <sub>P</sub> = 1 ms	I <sub>CRM</sub>	50	A
Gate-emitter peak voltage		V <sub>GES</sub>	± 20	V

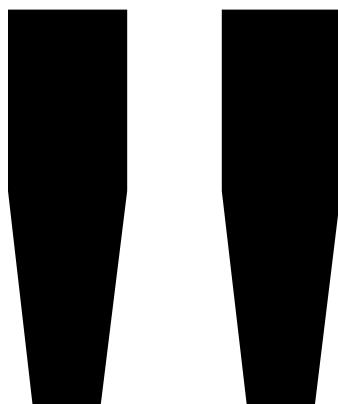
**Ch**
**r**
**l**

**Diode, Brake-Chopper  
Maximum Rated Values**

Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	$V_{RRM}$	1200	V
Continuous DC forward current		$I_F$	15	A
Repetitive peak forward current	$t_P = 1 \text{ ms}$	$I_{FRM}$	30	A

**Characteristic Values**

		$V_F$				V
Forward voltage	$I_F = 10 \text{ A}, V_{GE} = 0 \text{ V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 125^\circ\text{C}$			1.95 2.0		
Peak reverse recovery current	$V_R = 600 \text{ V}, I_F = 10 \text{ A},$ $V_{GE} = -15 \text{ V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 125^\circ\text{C}$	$I_{RM}$		14.5 13.6		A



**Module**
**Maximum Rated Values**

Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	VISOL	2.5	kV
Internal isolation	basic insulation (class 1, IEC 61140)		Al <sub>2</sub> O <sub>3</sub>	
Creepage distance	terminal to heatsink terminal to terminal		11.5 6.3	mm
Clearance	terminal to heatsink terminal to terminal		10 5	mm
Comperative tracking index		CTI	>200	

**Characteristic Values**

Fig. 1 output characteristic IGBT,Inverter

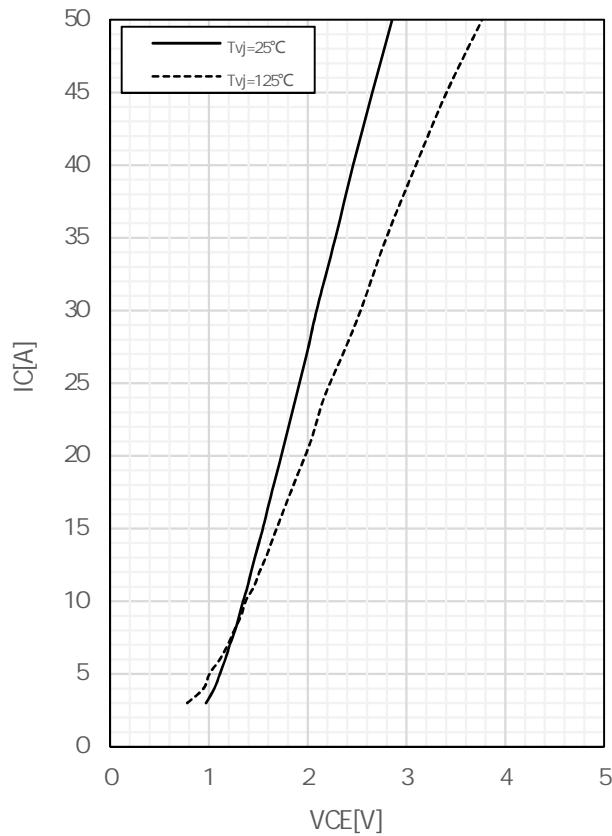


Fig.2 output characteristic IGBT,Inverter

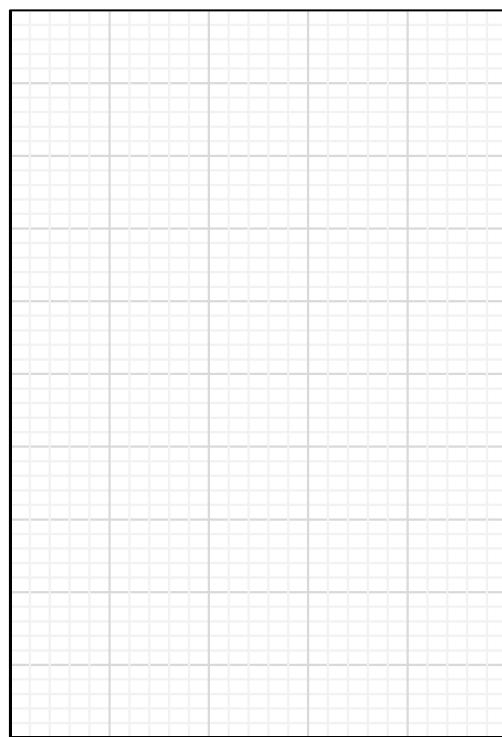


Fig. 3 transfer characteristic IGBT,Inverter

Fig. 4 switching losses IGBT,Inverter



**LGM25PJ120E2T1S**

Fig. 5 switching losses IGBT,Inverter

Fig. 6 transient thermal impedance IGBT,Inverter

Fig. 7 NTC-Thermistor-temperature characteristic

Fig. 9 switching losses Diode, Inverter

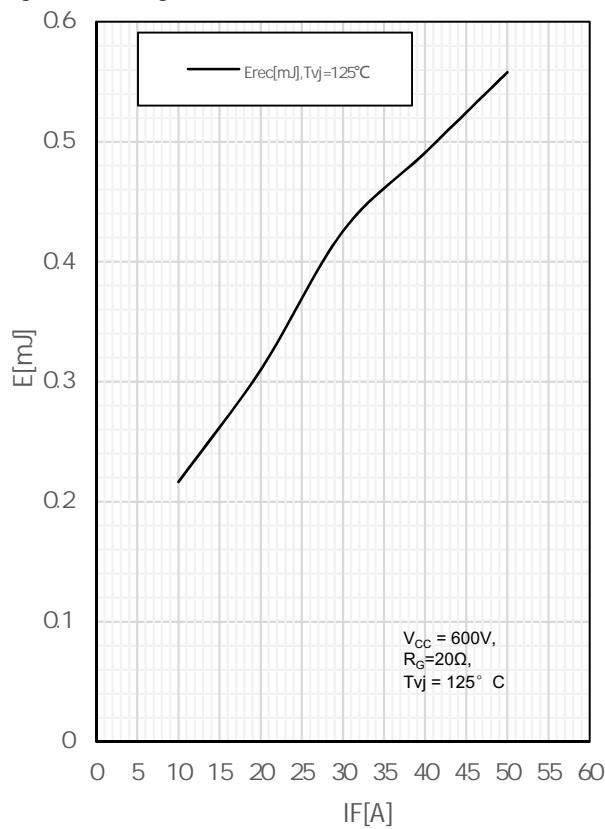


Fig. 10 switching losses Diode, Inverter

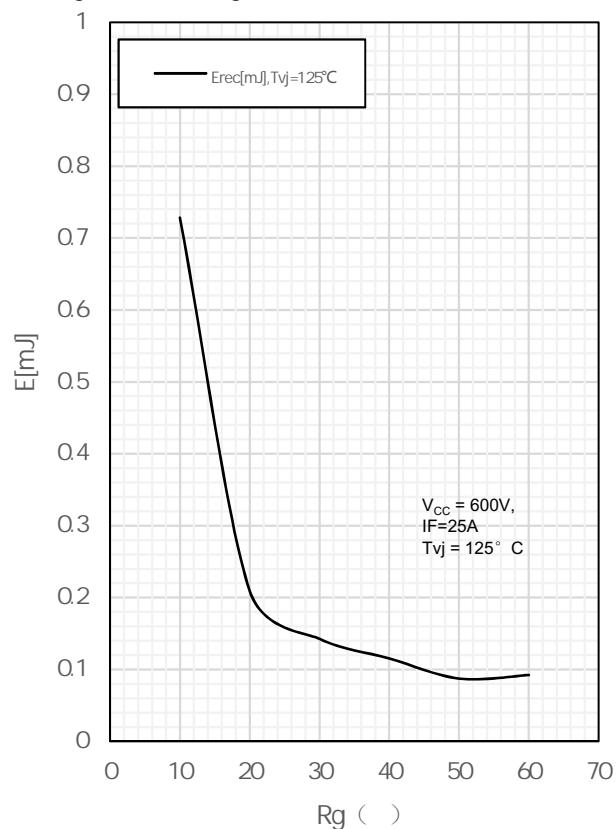


Fig. 11 transient thermal impedance Diode, Inverter

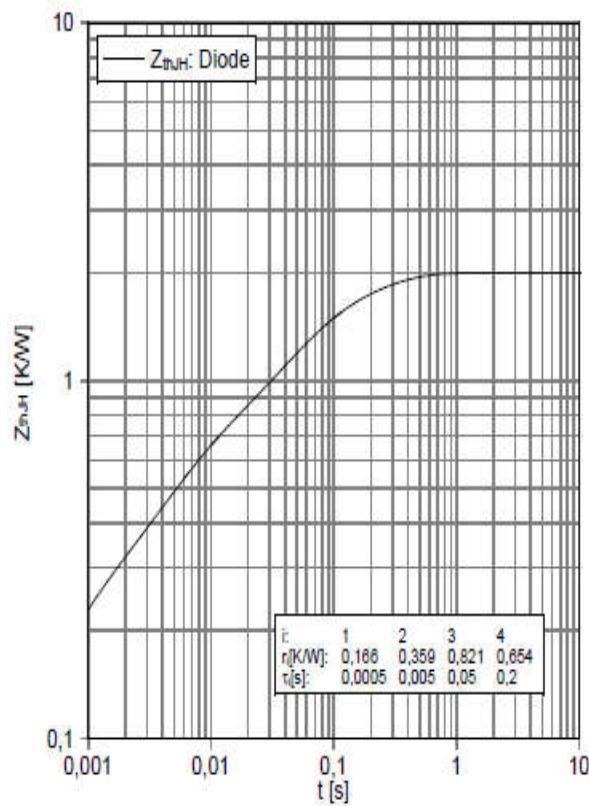


Fig. 12 forward characteristic of Diode, Rectifier

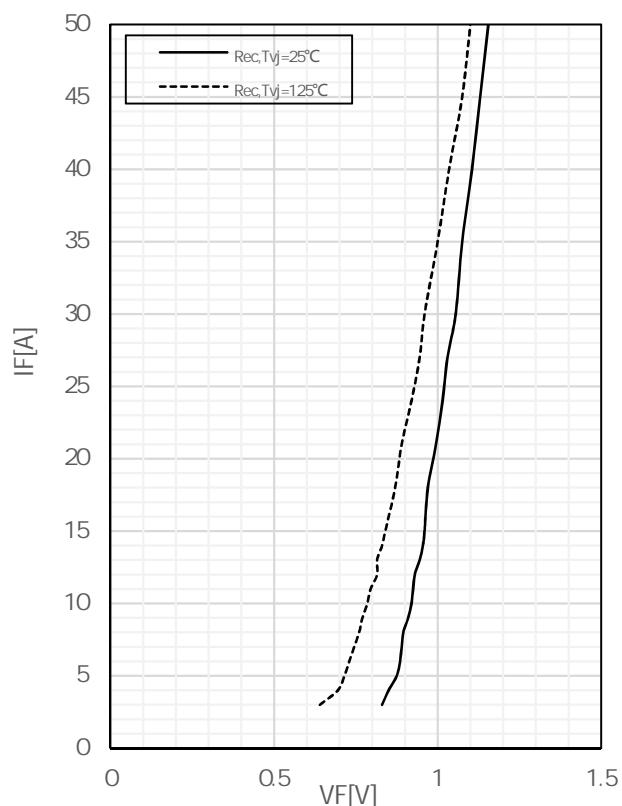


Fig. 13 output characteristic IGBT, Brake-Chopper

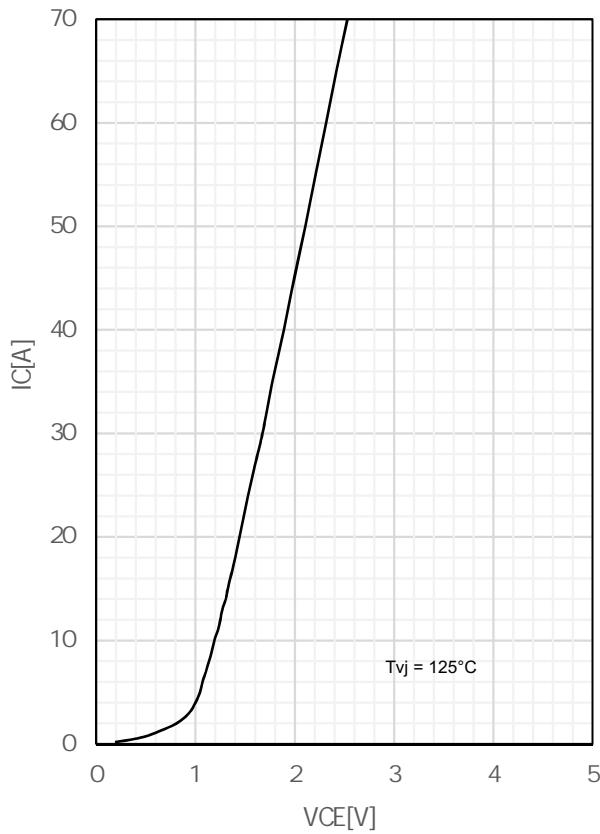
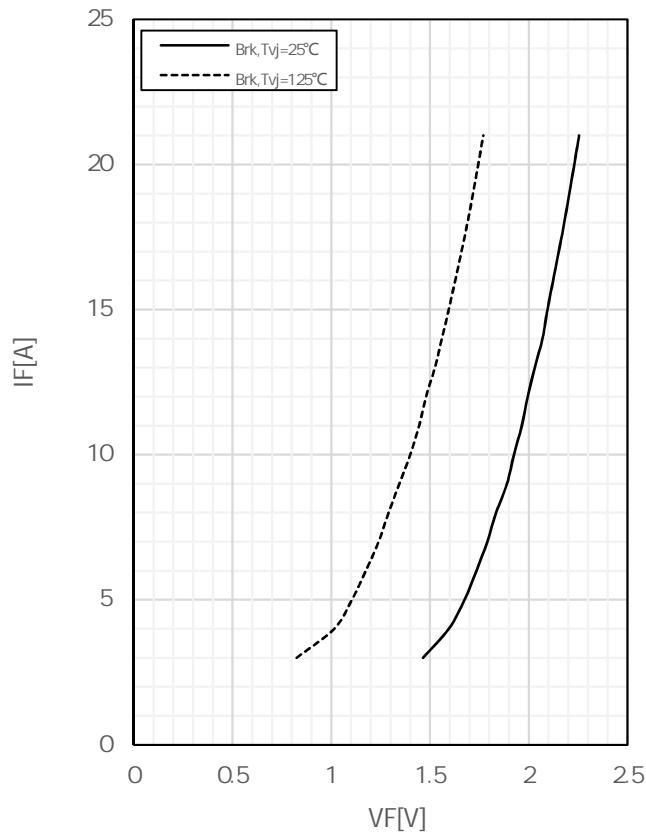


Fig. 14 forward characteristic of Diode, Brake-Chopper



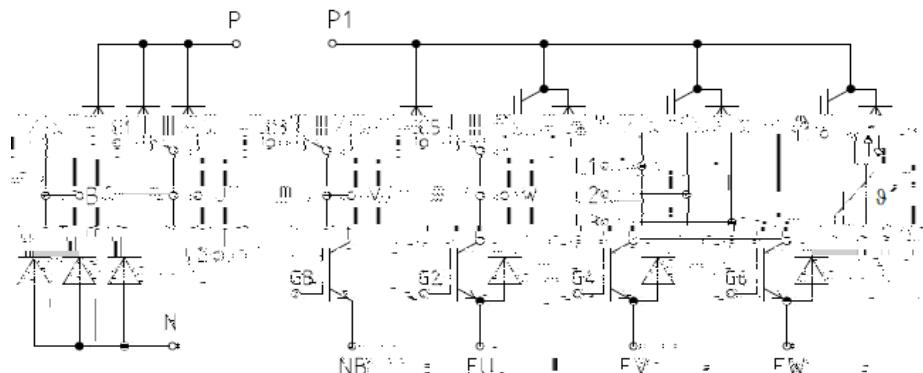


LUXIN · SEMI

上海聯芯電子科技有限公司

**LGM25PJ120E2T1S**

## Circuit diagram



## Package outlines (mm)

